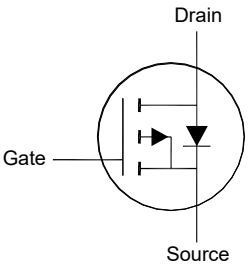
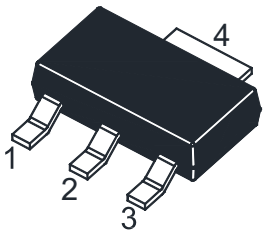
WTQ06P2K0L-AH

P-Channel Enhancement Mode Power MOSFET

Features

- AEC-Q101 Qualified
- Surface-mounted package
- Halogen and Antimony Free(HAF), RoHS compliant





1.Gate 2.Drain 3.Source 4.Drain
SOT-223 Plastic Package

Applications

- High speed Switching
- Portable appliances
- Battery management
- DC-DC converters for Telecom and Computer

Key Parameters

Parameter	Value	Unit
$-BV_{DSS}$	60	V
$R_{DS(ON)}$ Max	200 @ $-V_{GS}$ = 10 V	mΩ
	300 @ $-V_{GS}$ = 4.5 V	mΩ
$-V_{GS(th)}$ typ	1.8	V
Q_g typ	9 @ $-V_{GS}$ = 10 V	nC

Absolute Maximum Ratings (at T_a = 25℃ unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		$-V_{DS}$	60	V
Gate-Source Voltage		V_{GS}	± 20	V
Drain Current	T_a = 25℃ T_a = 100℃	$-I_D$	3 2	A
Peak Drain Current, Pulsed [1]		$-I_{DM}$	12	A
Power Dissipation		P_D	1.25	W
Single-Pulse Avalanche Current		$-I_{AS}$	12	A
Single-Pulse Avalanche Energy [2]		E_{AS}	7.2	mJ
Operating Junction and Storage Temperature Range		T_j, T_{stg}	- 55 to + 150	℃

Thermal Characteristics

Parameter		Symbol	Max.	Unit
Thermal Resistance-Junction to Ambient [3]	t < 10 s	$R_{\theta JA}$	60	℃/W
Thermal Resistance-Junction to Ambient [3]	Steady State		100	℃/W

[1] Pulse Test: Pulse Width ≤ 100 μs, Duty Cycle ≤ 2%, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ = 150°C.

[2] Limited by $T_{J(MAX)}$, starting T_J = 25 °C, L = 0.1 mH, R_g = 25 Ω, $-I_D$ = 12 A, V_{GS} = 10 V.

[3] Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

Dated: 14/10/2020 Rev: 01

Characteristics at T_a = 25℃ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $-I_D$ = 250 µA	$-V_{(BR)DSS}$	60	-	-	V
Zero Gate Voltage Drain Current at $-V_{DS}$ = 48 V	$-I_{DSS}$	-	-	1	µA
Gate-Source Leakage at V_{GS} = ± 20 V	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at V_{DS} = V_{GS}, $-I_D$ = 250 µA	$-V_{GS(th)}$	1	-	3	V
Drain-Source On-State Resistance at $-V_{GS}$ = 10 V, $-I_D$ = 3 A at $-V_{GS}$ = 4.5 V, $-I_D$ = 2 A	$R_{DS(on)}$	- -	155 -	200 300	mΩ
DYNAMIC PARAMETERS					
Gate Resistance at $-V_{DS}$ = 0, V_{GS} = 0, f = 1 MHz	R_g	-	18	-	Ω
Input Capacitance at $-V_{DS}$ = 30 V, V_{GS} = 0 V, f = 1 MHz	C_{iss}	-	589	-	pF
Output Capacitance at $-V_{DS}$ = 30 V, V_{GS} = 0 V, f = 1 MHz	C_{oss}	-	35	-	pF
Reverse Transfer Capacitance at $-V_{DS}$ = 30 V, V_{GS} = 0 V, f = 1 MHz	C_{rss}	-	8	-	pF
Total Gate Charge at $-V_{DS}$ = 20 V, $-V_{GS}$ = 10 V, $-I_D$ = 1.5 A	Q_g	-	9	-	nC
Gate-Source Charge at $-V_{DS}$ = 20 V, $-V_{GS}$ = 10 V, $-I_D$ = 1.5 A	Q_{gs}	-	2	-	nC
Gate-Drain Charge at $-V_{DS}$ = 20 V, $-V_{GS}$ = 10 V, $-I_D$ = 1.5 A	Q_{gd}	-	1.3	-	nC
Turn-On Delay Time at $-V_{DD}$ = 15 V, $-V_{GS}$ = 10 V, $-I_D$ = 1 A, R_g = 24 Ω	$t_{d(on)}$	-	18	-	ns
Turn-On Rise Time at $-V_{DD}$ = 15 V, $-V_{GS}$ = 10 V, $-I_D$ = 1 A, R_g = 24 Ω	t_r	-	14	-	ns
Turn-Off Delay Time at $-V_{DD}$ = 15 V, $-V_{GS}$ = 10 V, $-I_D$ = 1 A, R_g = 24 Ω	$t_{d(off)}$	-	28	-	ns
Turn-Off Fall Time at $-V_{DD}$ = 15 V, $-V_{GS}$ = 10 V, $-I_D$ = 1 A, R_g = 24 Ω	t_f	-	7	-	ns
Body-Diode PARAMETERS					
Body Diode Voltage at $-I_S$ = 1 A	$-V_{SD}$	-	-	1	V
Body-Diode Continuous Current	$-I_S$	-	-	3	A
Body-Diode Continuous Current, Pulsed	$-I_{SM}$	-	-	12	A
Body Diode Reverse Recovery Time at $-I_S$ = 1.5 A, di/dt = 100 A / µs	t_{rr}	-	12.4	-	ns
Body Diode Reverse Recovery Charge at $-I_S$ = 1.5 A, di/dt = 100 A / µs	Q_{rr}	-	8	-	nC

Electrical Characteristics Curves

Fig. 1 Typical Output Characteristic

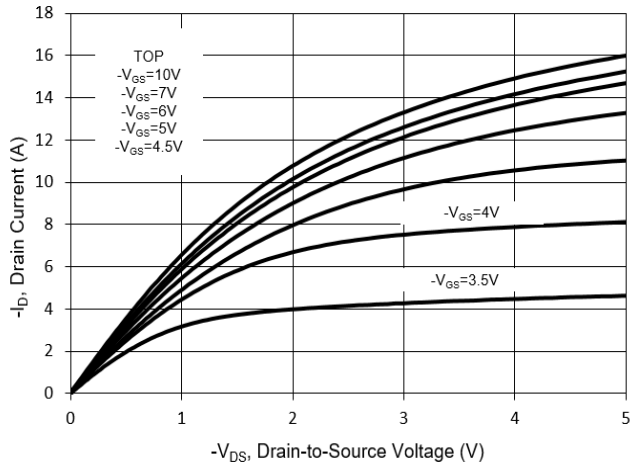


Fig. 2 Typical Transfer Characteristic

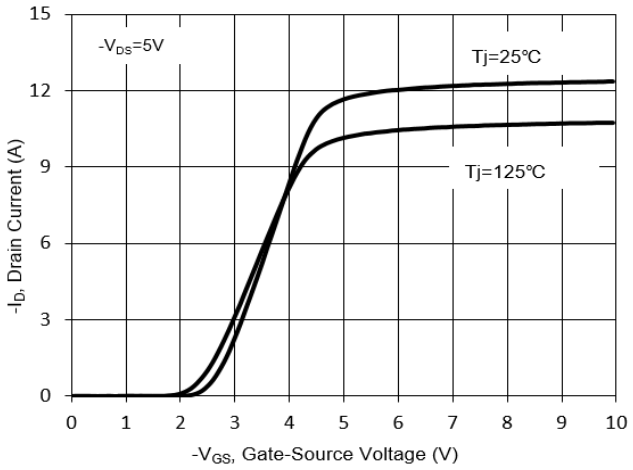


Fig. 3 on-Resistance vs. Gate Voltage

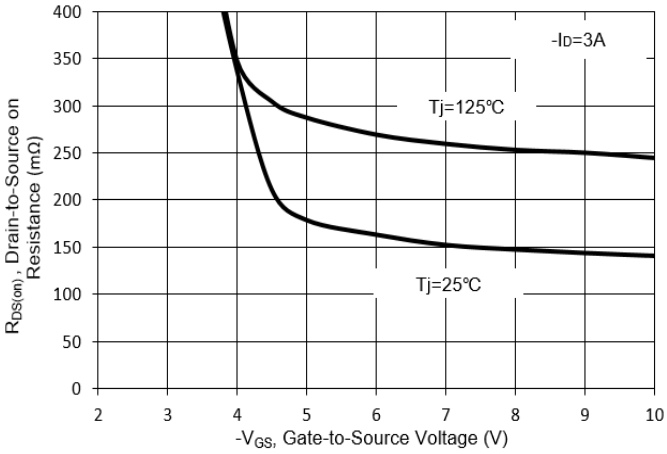


Fig. 4 on-Resistance vs.T_j

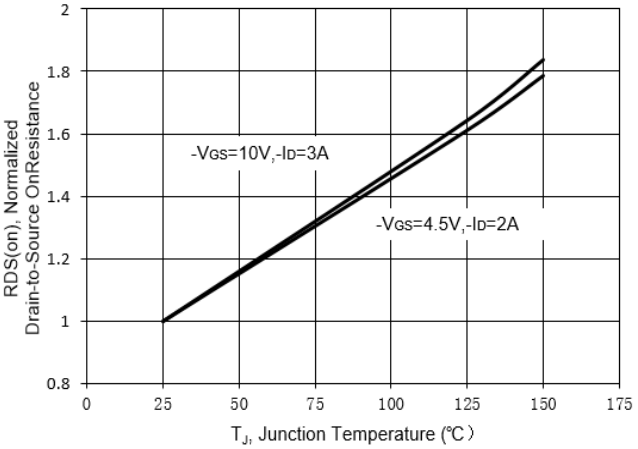


Fig. 5 on-Resistance vs. Drain Current

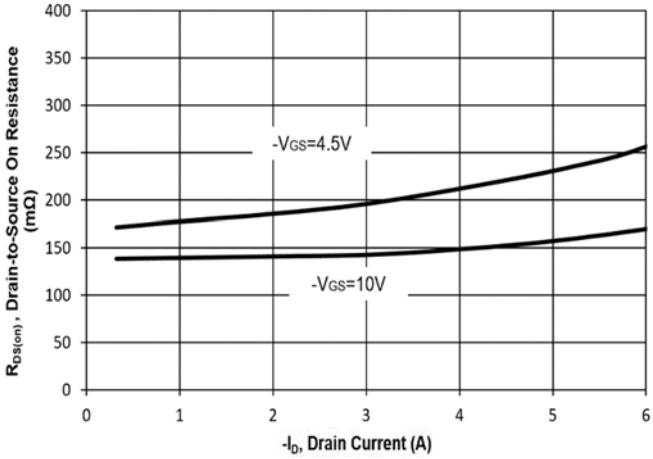
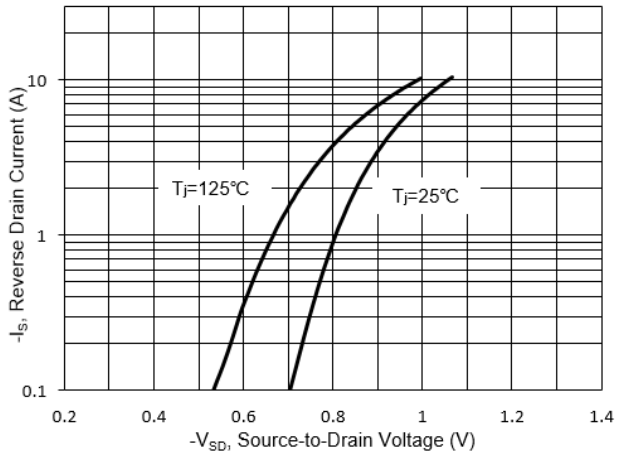


Fig. 6 Typical Forward Characteristic



Electrical Characteristics Curves

Fig. 7 $V_{(BR)DSS}$ vs. Junction Temperature

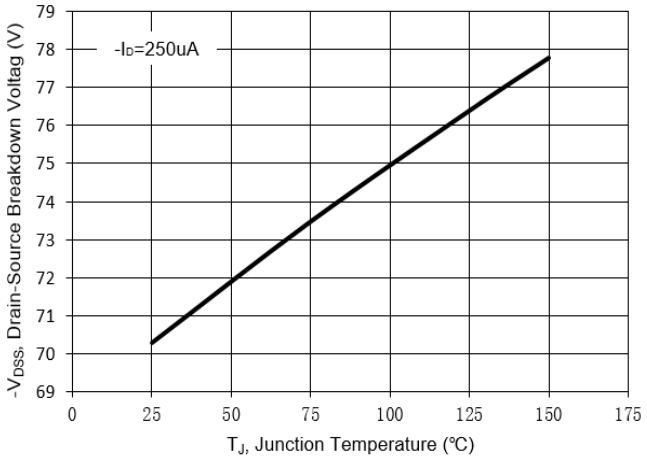


Fig. 8 Gate Threshold Variation vs. T_j

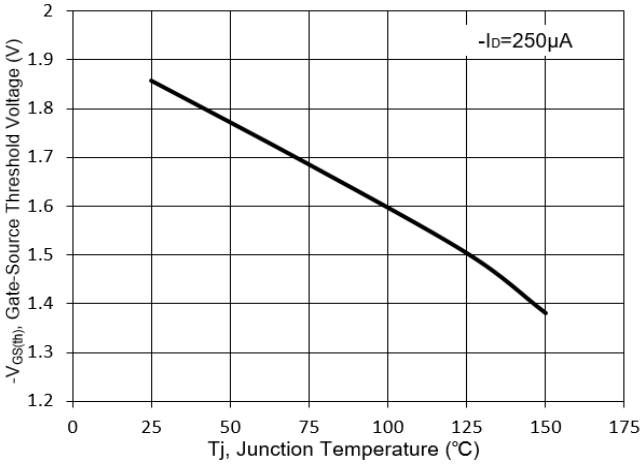


Fig. 9 Typical Junction Capacitance

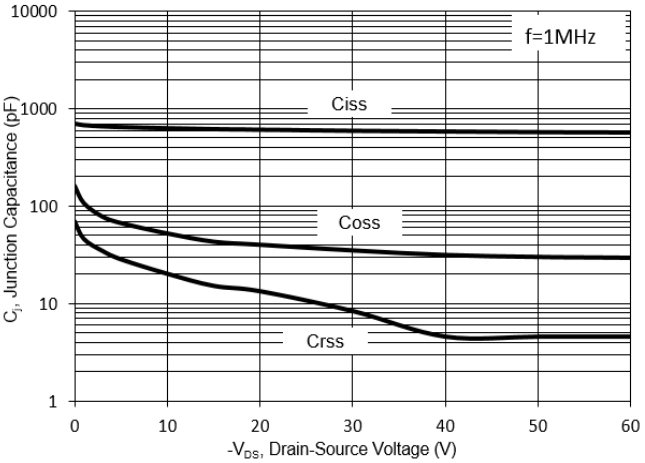


Fig. 10 Gate Charge

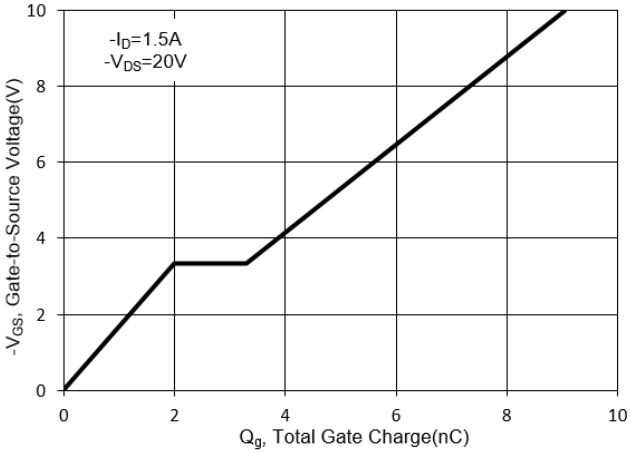


Fig. 11 Drain-Source Leakage Current vs. T_j

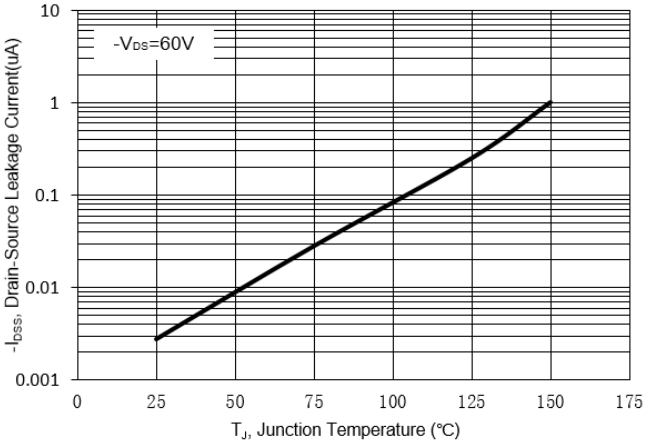
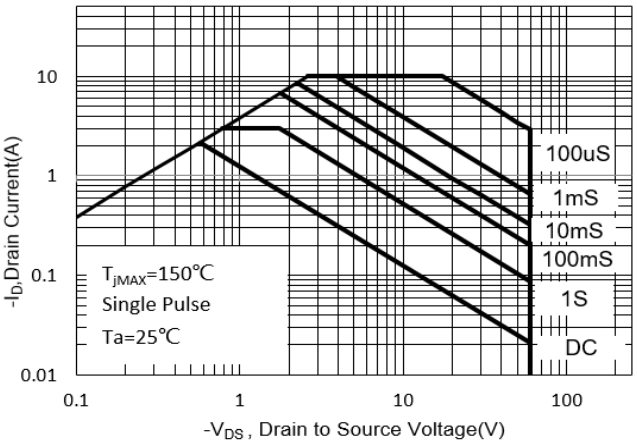
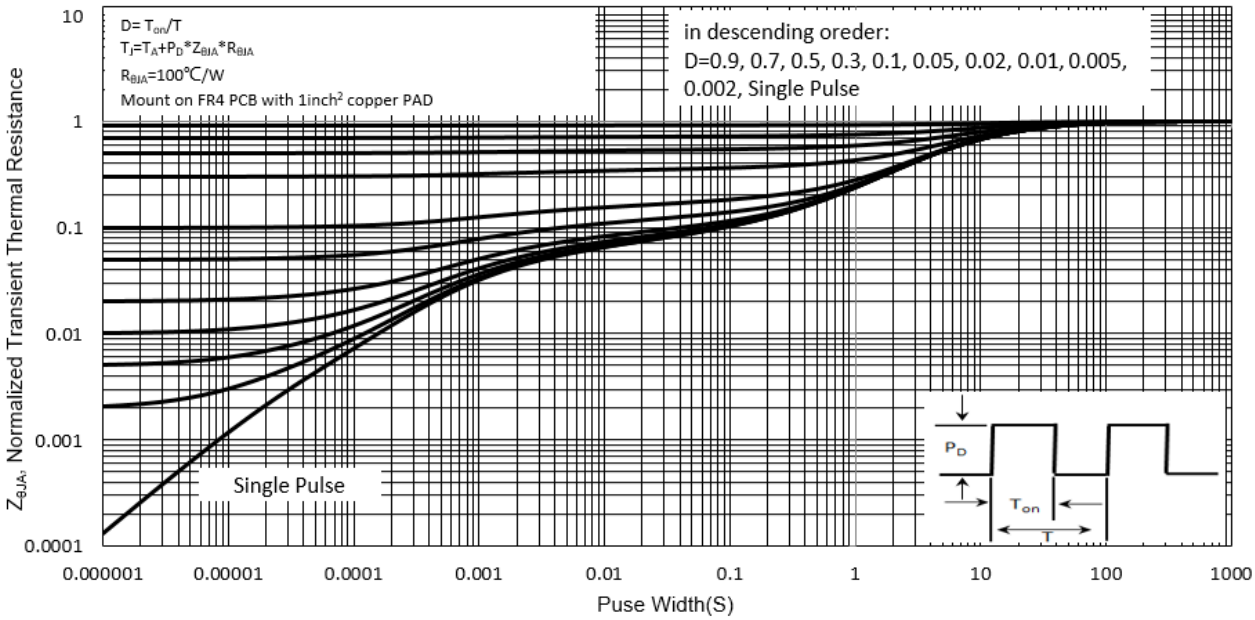


Fig. 12 Safe Operation Area



Electrical Characteristics Curves

Fig. 13 Transient Thermal Resistance （$Z_{\theta JA}$）



Test Circuits

Fig.1-1 Switching times test circuit

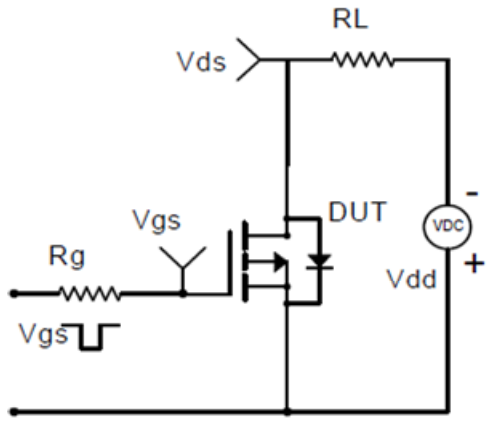


Fig.1-2 Switching Waveform

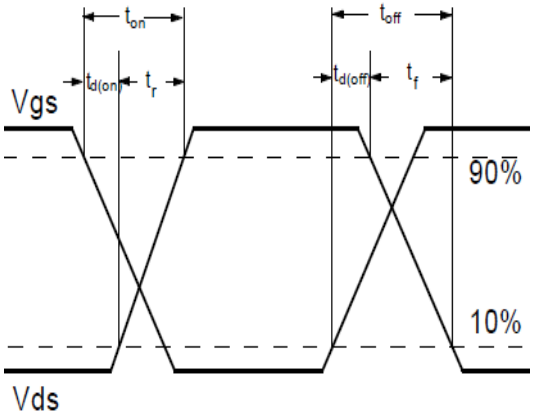


Fig.2-1 Gate charge test circuit

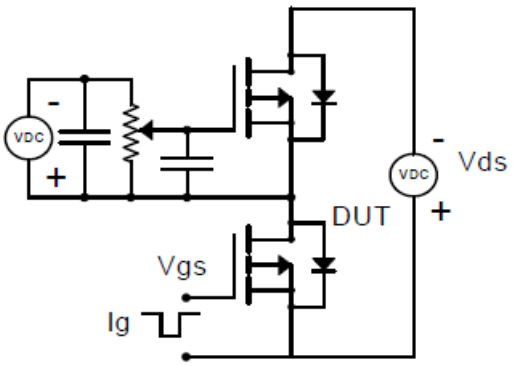


Fig.2-2 Gate charge waveform

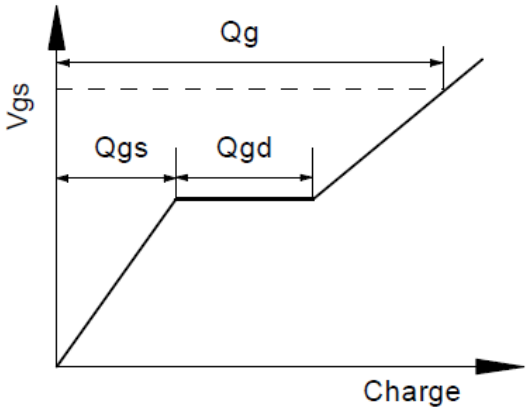


Fig.3-1 Avalanche test circuit

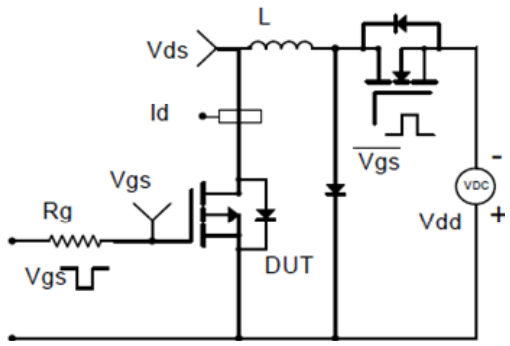
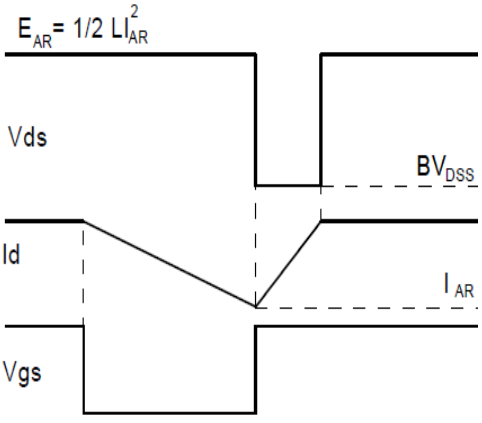
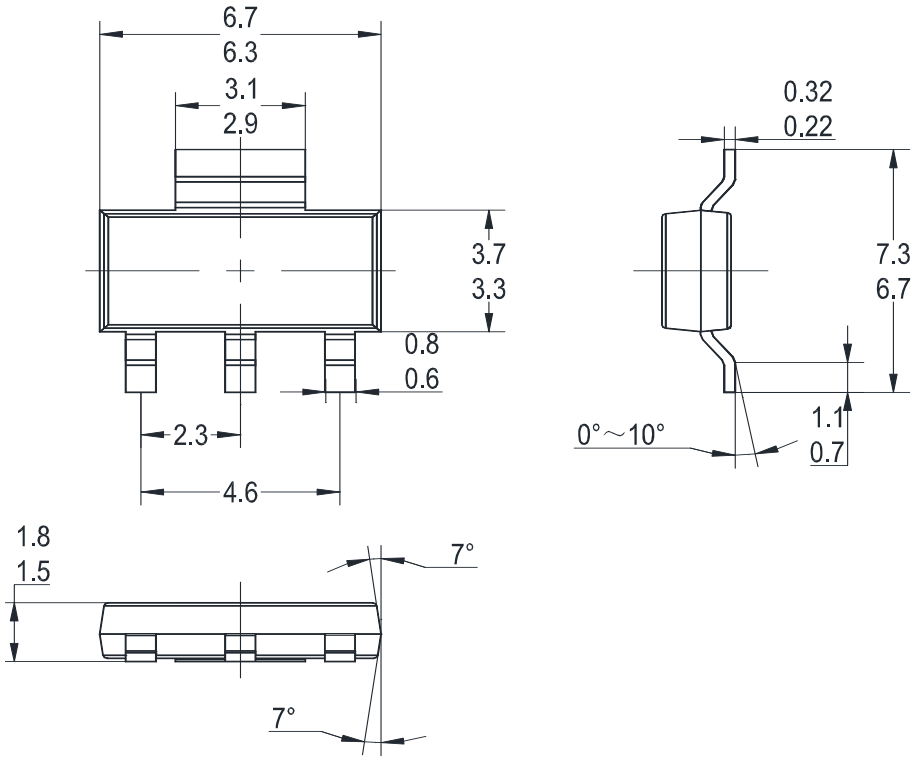


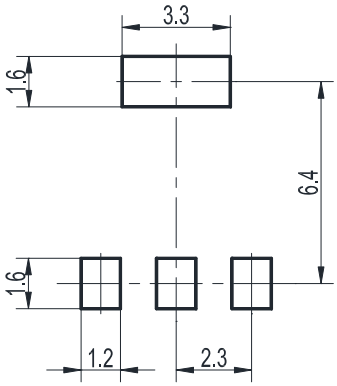
Fig.3-2 Avalanche waveform



Package Outline (Dimensions in mm) SOT-223



Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-223	12	8 ± 0.1	0.315 ± 0.004	330	13	3,000

Marking information

" TQ06P2K0L " = Part No.

" ********** " = Date Code Marking

Font type: Arial

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